



60V 175°C PNP LOW SAT MEDIUM POWER TRANSISTOR IN POWERDI5060-8

Features

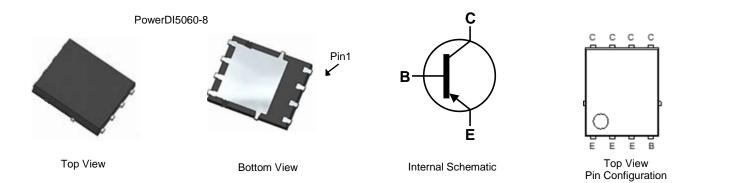
- BV_{CEO} > -60V
- I_C = -3A Continuous Collector Current
- I_{CM} = -8A Peak Pulse Current
- R_{CE(SAT)} < 120 mΩ
- Rated to +175°C—Ideal for High Ambient Temperature Environments
- Complementary Part DXTN3C60PS
- Meets Stringent Requirements of Automotive Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Finish—Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

Applications

- Power Management
- Load Switch
- Linear Mode Voltage Regulator
- Backlighting Applications



Ordering Information

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTP3C60PSQ-13	Automotive	DXTP3C60PS	13	12	2500

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

Marking Information



DXTP3 = Product Type Marking Code C60PS = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Base Current	Ι _Β	-1	A
Continuous Collector Current	Ι _C	-3	A
Peak Pulse Collector Current	I _{CM}	-8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	PD	5	W	
Thermal Desistance, lunction to Ambient	(Note 5)		40		
Thermal Resistance, Junction to Ambient	(Note 6)	R _{ØJA}	120	°C/W	
Thermal Desistance, lunction to Coop	(Note 5, 7)		2	°C/W	
Thermal Resistance, Junction to Case	(Note 6, 7)	R _{ejc}	12		
Operating and Storage Temperature Range		TJ, T _{STG}	-55 to +175	°C	

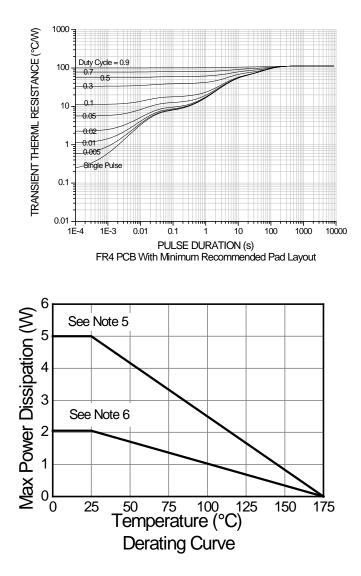
ESD Ratings (Note 8)

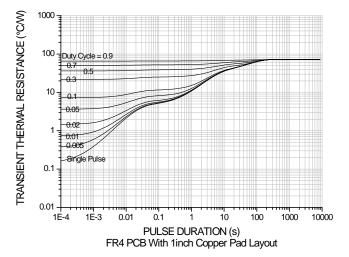
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	8000V	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400V	V	С

Notes: 5. For a device mounted with the collector lead on 25mm × 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still To a device inclution with the collector lead on 2011 a 220 copp air conditions whilst operating in a steady-state.
Same as Note 6 except mounted on minimum recommended pad layout.
Thermal resistance from junction to the top of the case.
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Typical Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)







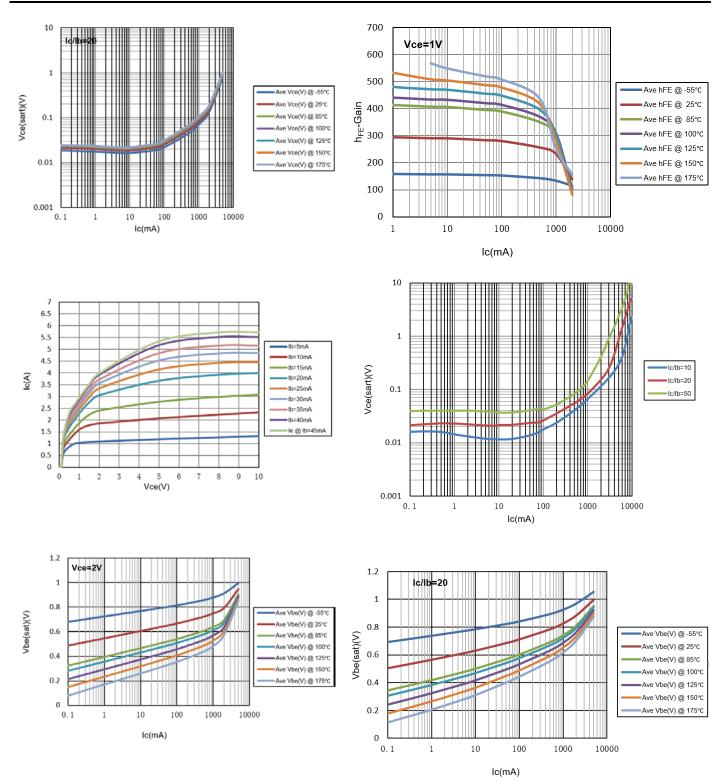
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-60	_	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-60	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	—	_	V	I _E = -100μA
Callester Dees Cutoff Current		_	_	-100	nA	V _{CB} = -48V
Collector-Base Cutoff Current	ICBO	_	—	-50	μA	V _{CB} = -48V @ Tj = 150°C
Emitter Cutoff Current	I _{EBO}	_	—	100	nA	V _{EB} = -7V
		_	-2.5	100		V _{CES} = -48V, T _A = +25°C
Collector-Emitter Cutoff Current	ICES	_	-2.4	—	nA	$V_{CES} = -14V, T_A = +40^{\circ}C$
		—	-50			V _{CES} = -14V, T _A = +105°C
ON CHARACTERISTICS (Note 9)	1		1	1		
		150	250	_		I _C = -500mA, V _{CE} = -2V
DC Current Gain	h _{FE}	150	225	—	_	$I_{C} = -1A, V_{CE} = -2V$
	UFE	80	130	—		$I_{C} = -2A, V_{CE} = -2V$
		35	75			$I_{C} = -3A, V_{CE} = -2V$
Collector-Emitter Saturation Voltage	Ver	_	-100	-225	mV	I _C = -1A, I _B = -50mA
	V _{CE(sat)}	_	-240	-360		I _C = -3A, I _B = -300mA
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	100	225	mΩ	I _C = -1A, I _B = -50mA
		_	80	120		I _C = -3A, I _B = -300mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	-0.8	-0.95	V	I _C = -1A, I _B = -50mA
Dase Emilier Galdraion Voltage		_	-1.02	-1.2		I _C = -2A, I _B = -200mA
Base-Emitter Turn-On Voltage	V _{BE(on)}	_	-0.7	-0.8	V	$I_{C} = -0.5A, V_{CE} = -2V$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f _T	_	135	—	MHz	$V_{CE} = -10V, I_C = -100mA, f = 100MHz$
Output Capacitance	Cobo	_	42	—	pF	V _{CB} = -10V, f = 1МНz
Delay Time	t _d	_	15	—	ns	
Rise Time	tr		220	_	ns	
Turn-On Time	t _(on)	_	235	_	ns	V _{CC} = -12.5V, I _C = 3A
Storage Time	ts	-	160	—	ns	I _{B1} = -I _{B2} = -0.150A
Fall Time	t _f		185	—	ns	
Turn-Off Time	t _(off)	_	345	_	ns	

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



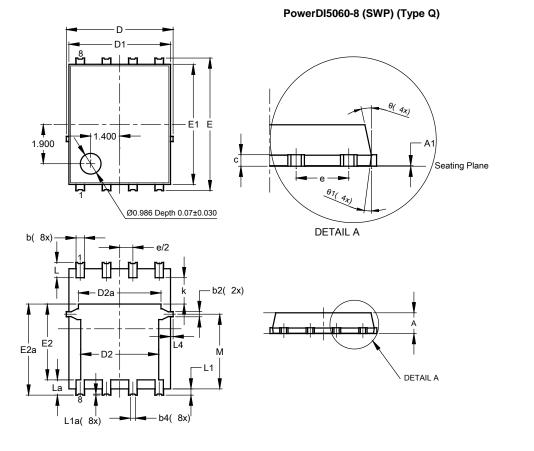
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

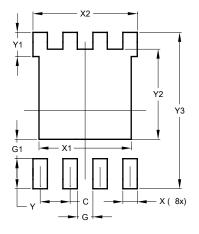


PowerDI5060-8 (SWP) (Type Q)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	-		
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF			
c	0.230	0.330	0.277		
D	5	.15 BS0	2		
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78 4.18 3.98				
E	6.40 BSC				
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
e	1.27BSC				
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
М	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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